

# Ming-Yen Kao

## List of Publications by Year in descending order

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citing authors

#	ARTICLE	IF	CITATIONS
1	Deep-Learning-Assisted Physics-Driven MOSFET Current-Voltage Modeling. IEEE Electron Device Letters, 2022, 43, 974-977.	3.9	32
2	Deep Learning-Based BSIM-CMG Parameter Extraction for 10-nm FinFET. IEEE Transactions on Electron Devices, 2022, 69, 4765-4768.	3.0	17
3	Electric Field-Induced Permittivity Enhancement in Negative-Capacitance FET. IEEE Transactions on Electron Devices, 2021, 68, 1346-1351.	3.0	10
4	Energy Storage and Reuse in Negative Capacitance. IEEE Transactions on Electron Devices, 2021, 68, 1861-1865.	3.0	2
5	BSIM Compact Model of Quantum Confinement in Advanced Nanosheet FETs. IEEE Transactions on Electron Devices, 2020, 67, 730-737.	3.0	38
6	Design Optimization Techniques in Nanosheet Transistor for RF Applications. IEEE Transactions on Electron Devices, 2020, 67, 4515-4520.	3.0	26
7	Analysis and Modeling of Polarization Gradient Effect on Negative Capacitance FET. IEEE Transactions on Electron Devices, 2020, 67, 4521-4525.	3.0	13
8	BSIM-HV: High-Voltage MOSFET Model Including Quasi-Saturation and Self-Heating Effect. IEEE Transactions on Electron Devices, 2019, 66, 4258-4263.	3.0	23
9	Characterization and Modeling of Flicker Noise in FinFETs at Advanced Technology Node. IEEE Electron Device Letters, 2019, 40, 985-988.	3.9	28
10	Spacer Engineering in Negative Capacitance FinFETs. IEEE Electron Device Letters, 2019, 40, 1009-1012.	3.9	36
11	Optimization of NCFET by Matching Dielectric and Ferroelectric Nonuniformly Along the Channel. IEEE Electron Device Letters, 2019, 40, 822-825.	3.9	16
12	Analysis and Modeling of Inner Fringing Field Effect on Negative Capacitance FinFETs. IEEE Transactions on Electron Devices, 2019, 66, 2023-2027.	3.0	37
13	Proposal for Capacitance Matching in Negative Capacitance Field-Effect Transistors. IEEE Electron Device Letters, 2019, 40, 463-466.	3.9	66
14	Engineering Negative Differential Resistance in NCFETs for Analog Applications. IEEE Transactions on Electron Devices, 2018, 65, 2033-2039.	3.0	79
15	Modeling of Advanced RF Bulk FinFETs. IEEE Electron Device Letters, 2018, 39, 791-794.	3.9	17
16	Effect of Polycrystallinity and Presence of Dielectric Phases on NC-FinFET Variability. , 2018, , .		14
17	Negative-Capacitance FinFETs: Numerical Simulation, Compact Modeling and Circuit Evaluation. , 2018, , .		9
18	Variation Caused by Spatial Distribution of Dielectric and Ferroelectric Grains in a Negative Capacitance Field-Effect Transistor. IEEE Transactions on Electron Devices, 2018, 65, 4652-4658.	3.0	29

#	ARTICLE	IF	CITATIONS
19	NCFET Design Considering Maximum Interface Electric Field. IEEE Electron Device Letters, 2018, 39, 1254-1257.	3.9	33
20	Tensile-strained Ge/SiGe multiple quantum well microdisks. Photonics Research, 2017, 5, B7.	7.0	9
21	Strained Pseudomorphic Ge <sub>1-x</sub> Sn <sub>x</sub> Multiple Quantum Well Microdisk Using SiN <sub>y</sub> Stressor Layer. ACS Photonics, 2016, 3, 2231-2236.	6.6	23